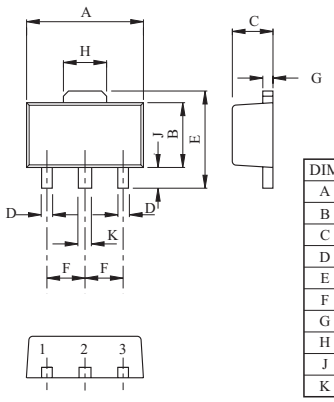
HIGH CURRENT APPLICATION.

FEATURES

- High Voltage : V_{CEO}=-120V.
- High Transition Frequency : f_T=120MHz(Typ.).
- 1W(Monunted on Ceramic Substrate).
- Small Flat Package.
- Complementary to KTC4373.



DIM	MILLIMETERS
A	4.70 MAX
B	2.50±0.20
C	1.70 MAX
D	0.45+0.15/-0.10
E	4.25 MAX
F	1.50±0.10
G	0.40 TYP
H	1.75 MAX
J	0.75 MIN
K	0.5+0.10/-0.05

1. BASE
2. COLLECTOR (HEAT SINK)
3. EMITTER

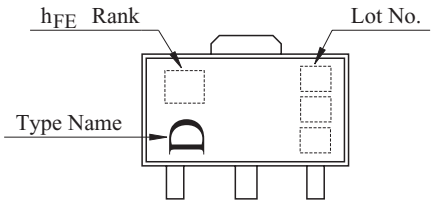
SOT-89

MAXIMUM RATING (Ta=25℃)

CHARACTERISTIC	SYMBOL	RATING	UNIT
Collector-Base Voltage	V_{CBO}	-120	V
Collector-Emitter Voltage	V_{CEO}	-120	V
Emitter-Base Voltage	V_{EBO}	-5	V
Collector Current	I_C	-800	mA
Base Current	I_B	-160	mA
Collector Power Dissipation	P_C	500	mW
	P_C*	1	W
Junction Temperature	T_j	150	℃
Storage Temperature Range	T_{stg}	-55～150	℃

P_C* : KTA1661 mounted on ceramic substrate (250mm²x0.8t)

Marking

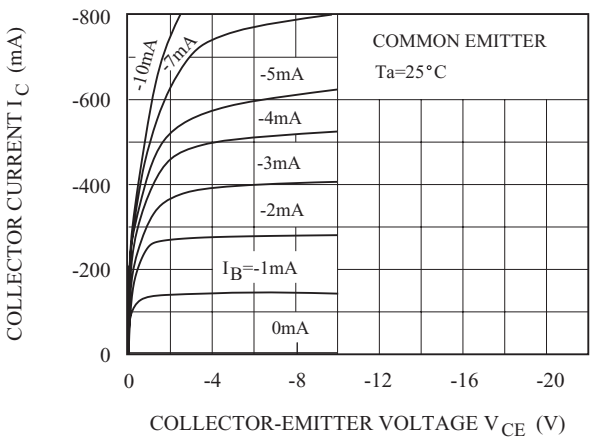


ELECTRICAL CHARACTERISTICS (Ta=25℃)

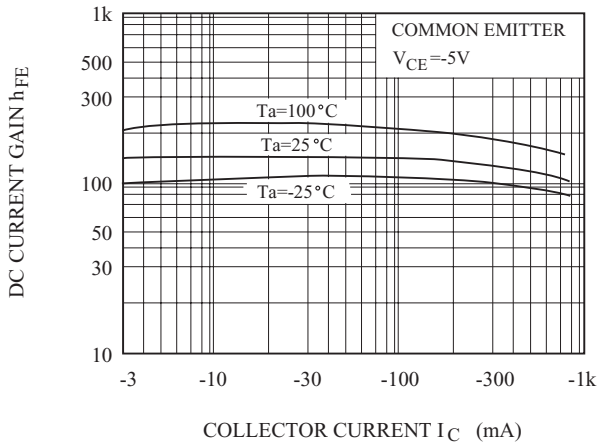
CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Collector Cut-off Current	I_{CBO}	V_{CB}=-120V, I_E=0	-	-	-100	nA
Emitter Cut-off Current	I_{EBO}	V_{EB}=5V, I_C=0	-	-	-100	nA
Collector-Emitter Breakdown Voltage	$V_{(BR)CEO}$	I_C=-10mA, I_B=0	-120	-	-	V
Emitter-Base Breakdown Voltage	$V_{(BR)EBO}$	I_E=-1mA, I_C=0	-5.0	-	-	V
DC Current Gain	h_{FE} (Note)	V_{CE}=-5V, I_C=-100mA	80	-	240	
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$	I_C=-500mA, I_B=-50mA	-	-	-1.0	V
Base-Emitter Voltage	V_{BE}	V_{CE}=-5V, I_C=-500mA	-	-	-1.0	V
Transition Frequency	f_T	V_{CE}=-5V, I_C=-100mA	-	120	-	MHz
Collector Output Capacitance	C_{ob}	V_{CB}=-10V, I_E=0, f=1MHz	-	-	30	pF

Note : h_{FE} Classification O:80～160, Y:120～240

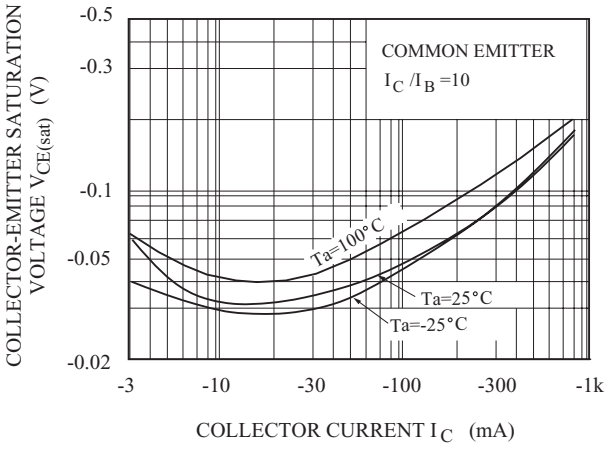
I_C - V_{CE}



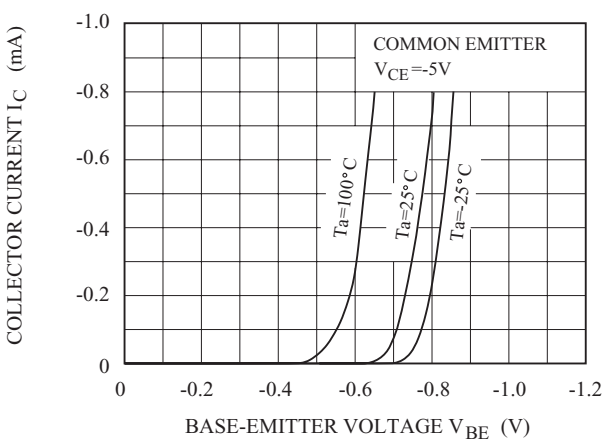
h_{FE} - I_C



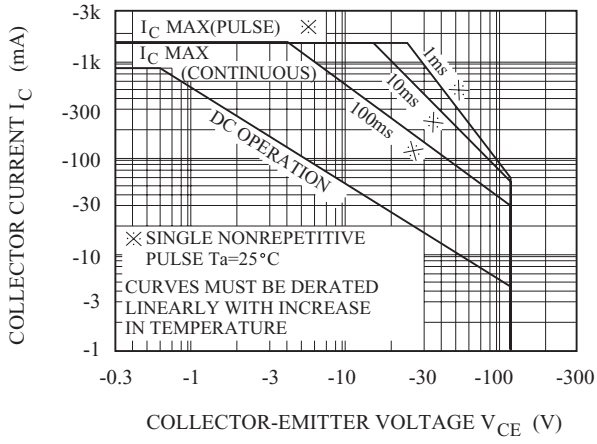
$V_{CE(sat)}$ - I_C



I_C - V_{BE}



SAFE OPERATING AREA



Pc - Ta